

Application No.: 10/826,003

Docket No.: JCLA12118

AMENDMENTS**In The Claims:**

Please amend the claims as follows:

Claims 1-6 (canceled)

7. (currently amended) A light-emitting diode package structure, comprising:

a semiconductor sub-mount having a first surface with a cavity therein;

a first patterned conductive-reflective film set up on a portion of the first surface,
a first sidewall of the cavity and a bottom surface of the cavity, wherein the first patterned
conductive-reflective film substantially covers the first sidewall of the cavity;

a second patterned conductive-reflective film set up on a portion of the first
surface, a second sidewall of the cavity and a bottom surface of the cavity, wherein the second
patterned conductive-reflective film substantially covers the second sidewall of the cavity; and

a light-emitting diode chip set up inside the cavity of the semiconductor sub-
mount, wherein the light-emitting diode has a first electrode and a second electrode electrically
connected to the first patterned conductive-reflective film and the second patterned conductive-
reflective film.

8. (original) The light-emitting diode package structure of claim 7, wherein the package
further comprises a pair of bumps set up between the first electrode of the light-emitting diode

Application No.: 10/826,003

Docket No.: JCLA12118

and the first patterned conductive-reflective film as well as the second electrode of the light-emitting diode and the second patterned conductive-reflective film.

9. (original) The light-emitting diode package structure of claim 8, wherein material constituting the bumps comprises lead-tin, gold-tin alloy or gold.

10. (original) The light-emitting diode package structure of claim 7, wherein the package further comprises a first bonding pad and a second bonding pad set up on the first patterned conductive-reflective film and the second patterned conductive-reflective film for connecting electrically with an external circuit board.

11. (original) The light-emitting diode package structure of claim 7, wherein the sidewall and the bottom surface of the cavity form an obtuse angle.

12. (original) The light-emitting diode package structure of claim 7, wherein material constituting the semiconductor sub-mount comprises silicon or gallium arsenide or SiC, zinc oxide.

Application No.: 10/826,003

Docket No.: JCLA12118

13. (original) The light-emitting diode package structure of claim 7, wherein the semiconductor sub-mount further comprises:

a first conductive type semiconductor sub-mount, wherein the first conductive type semiconductor sub-mount has a second conductive type region therein; and

an insulating layer set up on the first conductive type semiconductor sub-mount, wherein one of the electrodes is electrically connected to the second conductive type region but electrically isolated from the first conductive type semiconductor sub-mount through the insulating layer.

14. (original) The light-emitting diode package structure of claim 12, wherein the first conductive type semiconductor sub-mount is an N-doped material layer and the second conductive type region is a P-doped material layer.

15. (original) The light-emitting diode package structure of claim 12, wherein the first conductive type semiconductor sub-mount is a P-doped material layer and the second conductive type region is an N-doped material layer.